

**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**
**Features**

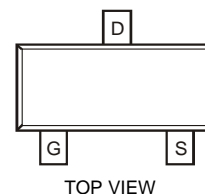
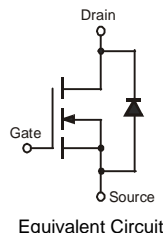
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 3 and 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23


**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	50	V
Drain-Gate Voltage $R_{GS} \leq 20K\Omega$	$V_{DGR}$	50	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	200	mA

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Power Dissipation (Note 1)	$P_d$	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 2)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	50	75	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	0.5	$\mu A$	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 2)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	1.2	1.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.4	3.5	$\Omega$	$V_{GS} = 10V, I_D = 0.22A$
Forward Transconductance	$g_{FS}$	100	—	—	mS	$V_{DS} = 25V, I_D = 0.2A, f = 1.0KHz$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	—	50	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	8.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	—	—	20	ns	$V_{DD} = 30V, I_D = 0.2A, R_{GEN} = 50\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	—	20	ns	

- Notes:
1. Device mounted on FR-5 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. Short duration pulse test used to minimize self-heating effect.
  3. No purposefully added lead. Halogen and Antimony Free.
  4. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or  $Sb_2O_3$  Fire Retardants.

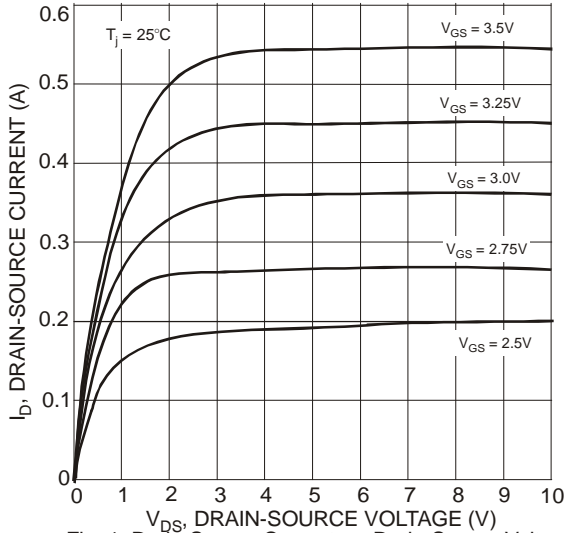


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

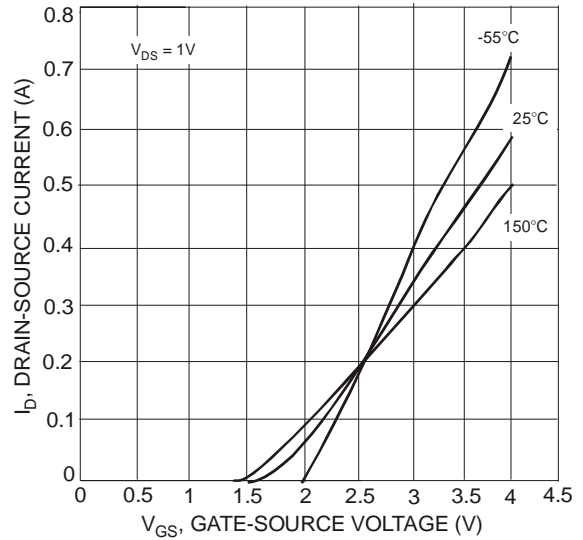


Fig. 2 Transfer Characteristics

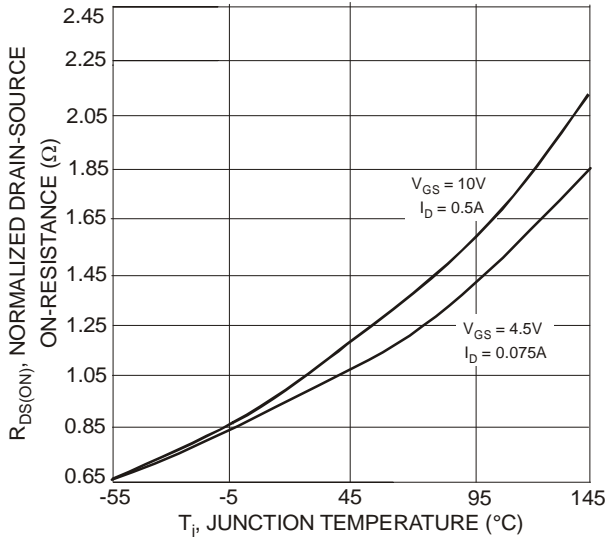


Fig. 3 Drain-Source On-Resistance vs. Junction Temperature

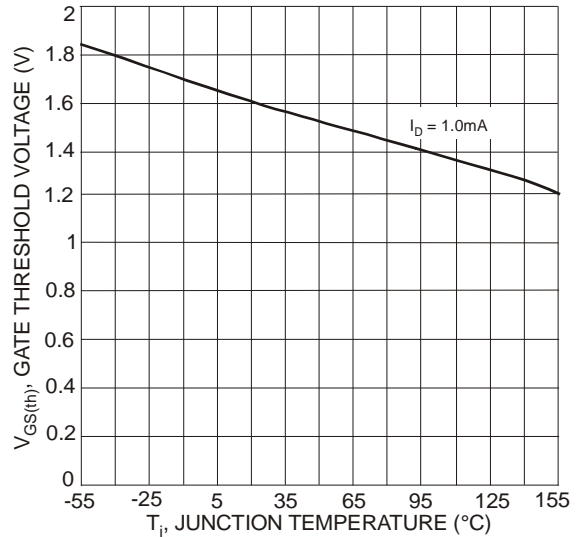


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

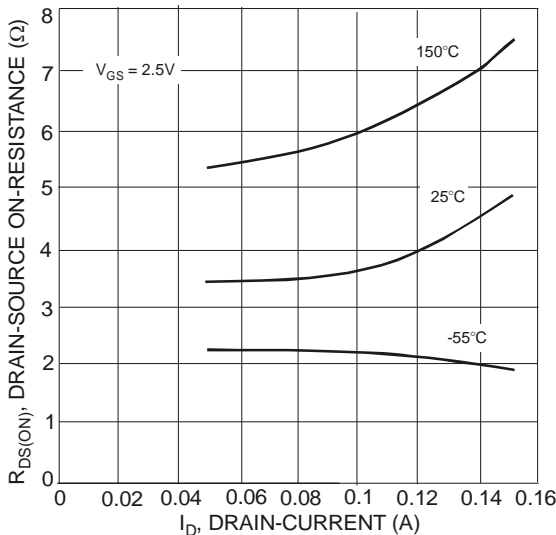


Fig. 5 Drain-Source On-Resistance vs. Drain-Current

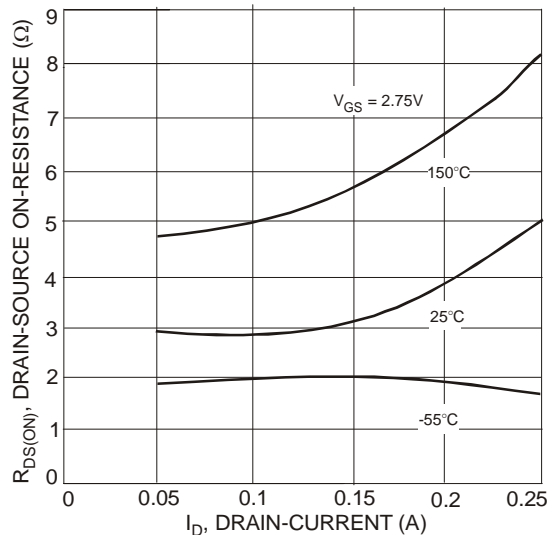


Fig. 6 Drain-Source On-Resistance vs. Drain-Current

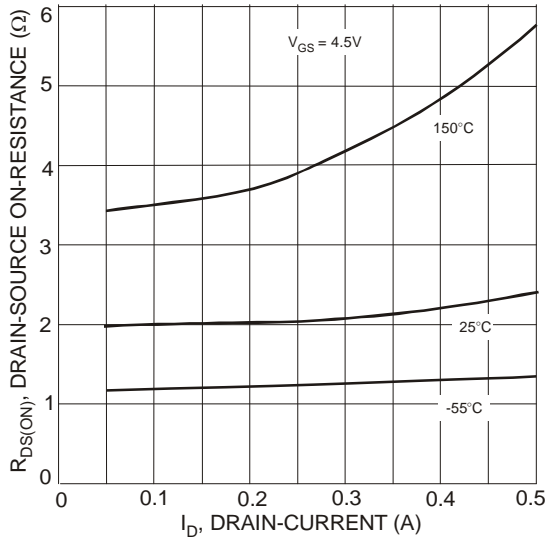


Fig. 7 Drain-Source On-Resistance vs. Drain-Current

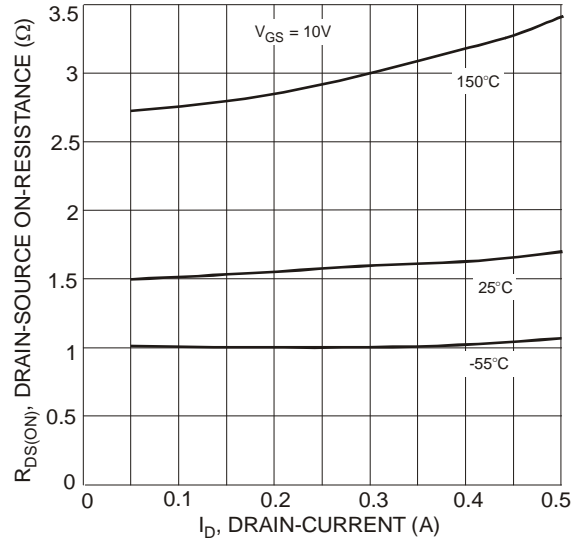


Fig. 8 Drain-Source On Resistance vs. Drain-Current

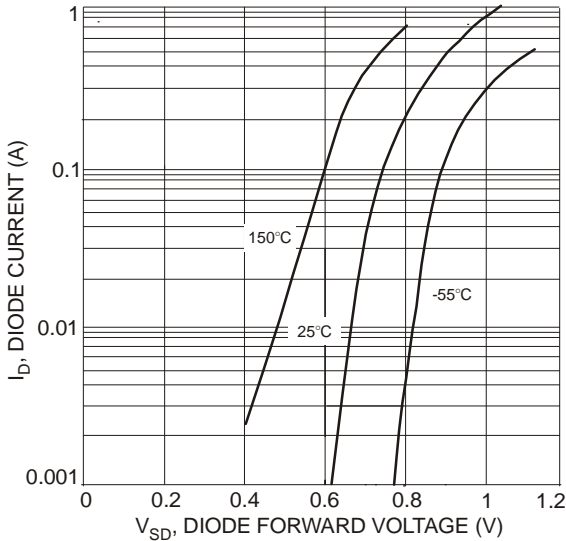


Fig. 9 Body Diode Current vs. Body Diode Voltage

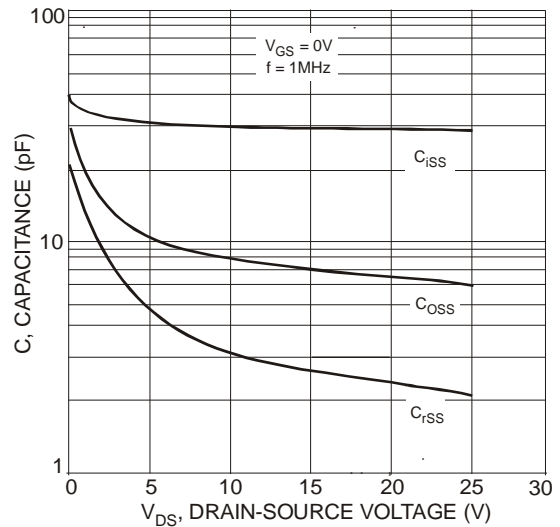


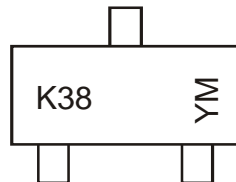
Fig. 10 Capacitance vs. Drain-Source Voltage

**Ordering Information** (Note 5)

Part Number	Case	Packaging
BSS138-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**

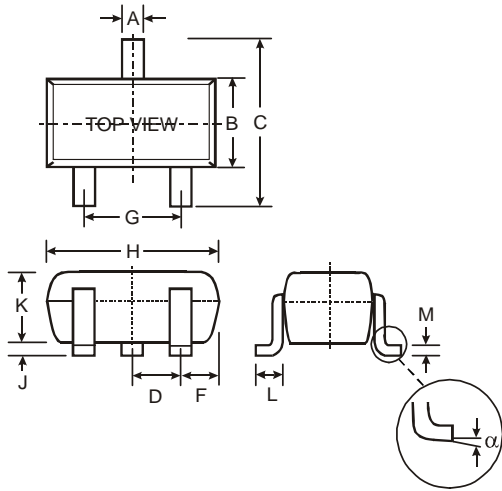


K38 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

Date Code Key

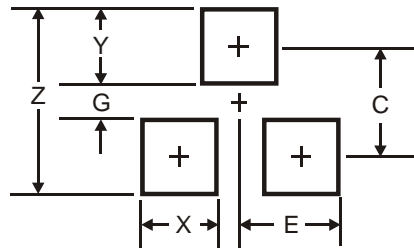
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec			
Code	1	2	3	4	5	6	7	8	9	O	N	D			

**Package Outline Dimensions**



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
F	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.4
G	0.7
X	0.9
Y	1.4
C	2.0
E	0.9

**IMPORTANT NOTICE**

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

**LIFE SUPPORT**

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.